



# EFC6601R

## N-Channel Power MOSFET 24V, 13A, 11.5mΩ, Dual EFCP

ON Semiconductor®

<http://onsemi.com>

### Features

- 2.5V drive
- Common-drain type
- 2KV ESD HBM
- Protection diode in
- Halogen free compliance

### Specifications

Absolute Maximum Ratings at Ta=25°C

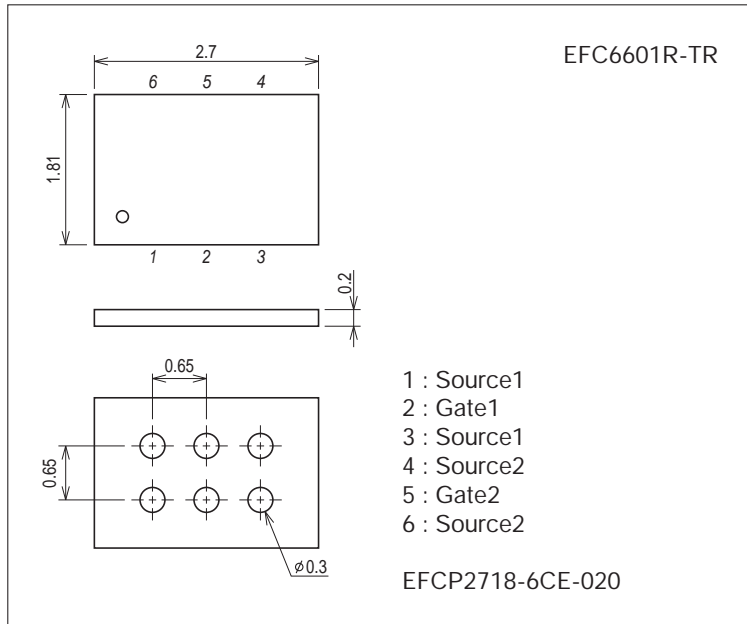
Parameter	Symbol	Conditions	Ratings	Unit
Source-to-Source Voltage	V <sub>SSS</sub>		24	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±12	V
Source Current (DC)	I <sub>S</sub>		13	A
Source Current (Pulse)	I <sub>SP</sub>	PW≤10μs, duty cycle≤1%	60	A
Total Dissipation	P <sub>T</sub>	When mounted on ceramic substrate (5000mm <sup>2</sup> ×0.8mm)	2.0	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### Package Dimensions

unit : mm (typ)

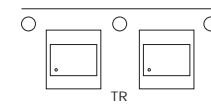
7073-001



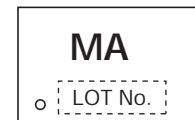
### Product & Package Information

- Package : EFCP
- JEITA, JEDEC : -
- Minimum Packing Quantity : 5,000 pcs./reel

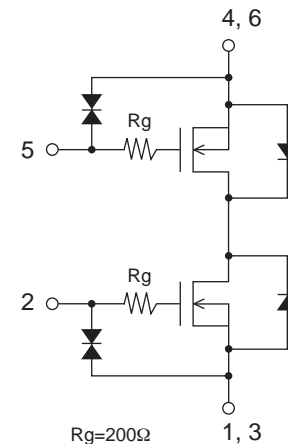
### Taping Type : TR



### Marking



### Electrical Connection



# EFC6601R

## Electrical Characteristics at Ta=25°C

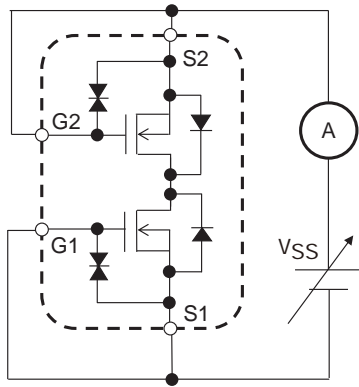
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Source-to-Source Breakdown Voltage	V(BR)SSS	I <sub>S</sub> =1mA, V <sub>GS</sub> =0V Test Circuit 1	24			V
Zero-Gate Voltage Source Current	I <sub>SSS</sub>	V <sub>SS</sub> =20V, V <sub>GS</sub> =0V Test Circuit 1			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>SS</sub> =0V Test Circuit 2			±1	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>SS</sub> =10V, I <sub>S</sub> =1mA Test Circuit 3	0.5		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>SS</sub> =10V, I <sub>S</sub> =3A Test Circuit 4		15.5		S
Static Source-to-Source On-State Resistance	R <sub>SS(on)1</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =4.5V Test Circuit 5	6.6	9.5	11.5	mΩ
	R <sub>SS(on)2</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =4.0V Test Circuit 5	7.0	10	12	mΩ
	R <sub>SS(on)3</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =3.8V Test Circuit 5	7.3	10.5	13	mΩ
	R <sub>SS(on)4</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =3.1V Test Circuit 5	8.0	11.5	15	mΩ
	R <sub>SS(on)5</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =2.5V Test Circuit 5	9.0	13	17	mΩ
Turn-ON Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =3A Test Circuit 7		280		ns
Rise Time	t <sub>r</sub>			630		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			53000		ns
Fall Time	t <sub>f</sub>			47000		ns
Total Gate Charge	Q <sub>g</sub>		V <sub>DD</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>S</sub> =13A Test Circuit 8		48	
Forward Source-to-Source Voltage	V <sub>F(S-S)</sub>	I <sub>S</sub> =3A, V <sub>GS</sub> =0V Test Circuit 6		0.76	1.2	V

## Ordering Information

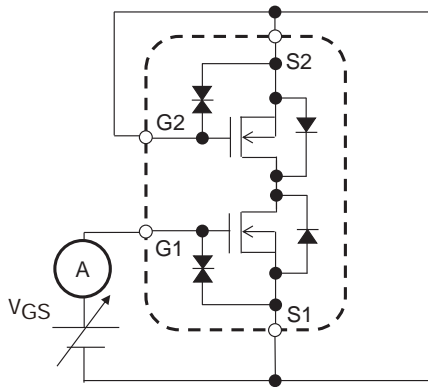
Device	Package	Shipping	memo
EFC6601R-TR	EFCP	5,000pcs./reel	Pb Free and Halogen Free

Test circuits are example of measuring FET1 side

Test Circuit 1  
ISSS

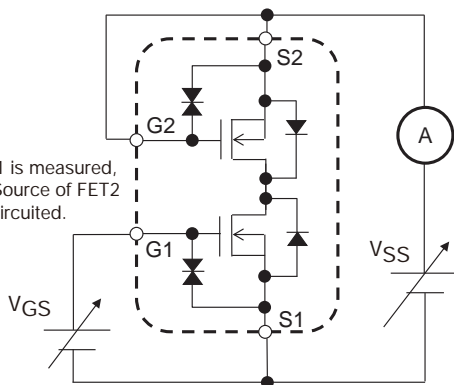


Test Circuit 2  
IGSS



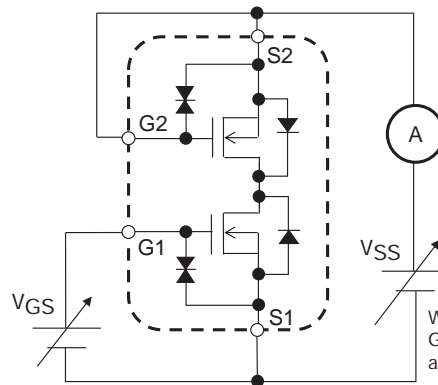
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 3  
VGS(off)



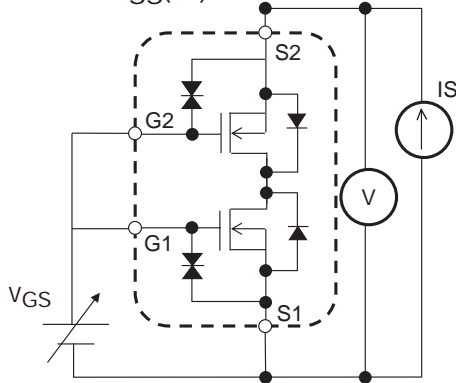
When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 4  
 $|y_{fs}|$

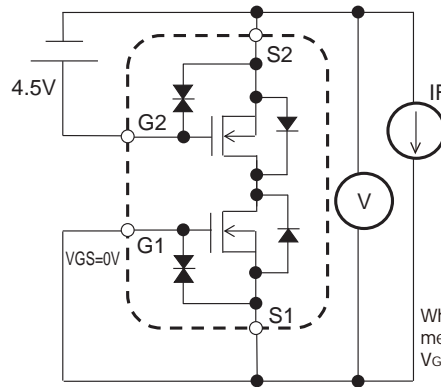


When FET1 is measured, Gate and Source of FET2 are short-circuited.

Test Circuit 5  
RSS(on)

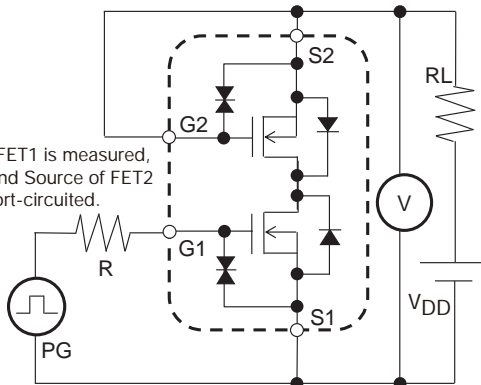


Test Circuit 6  
VF(S-S)



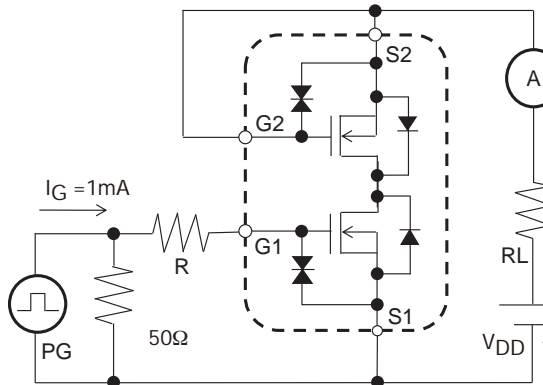
When FET1 is measured, +4.5V is added to Vgs of FET2.

Test Circuit 7  
 $t_d(on)$ ,  $t_r$ ,  $t_d(off)$ ,  $t_f$



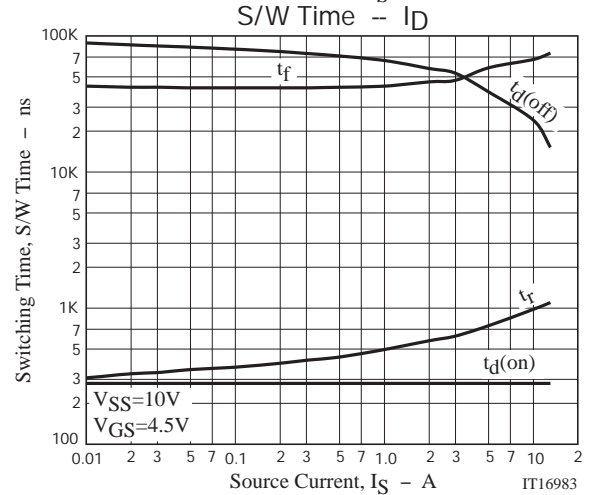
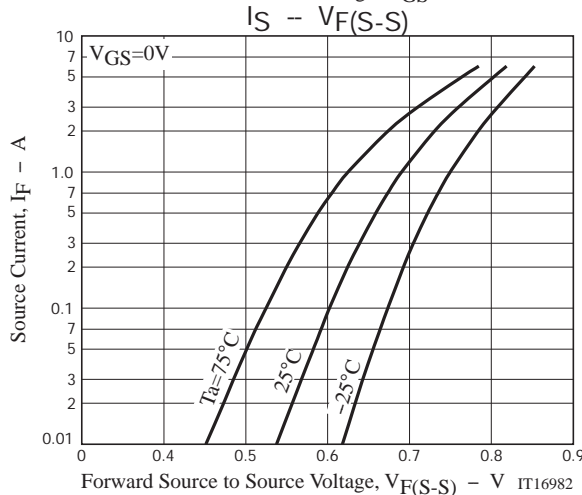
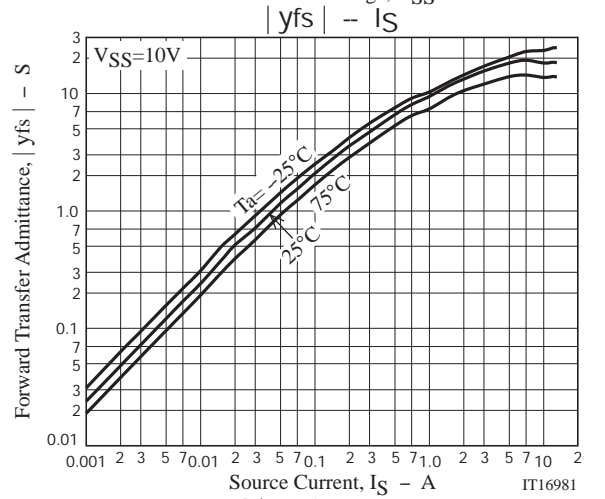
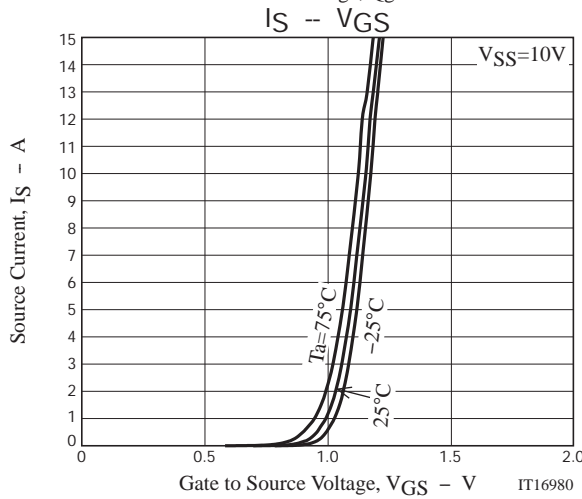
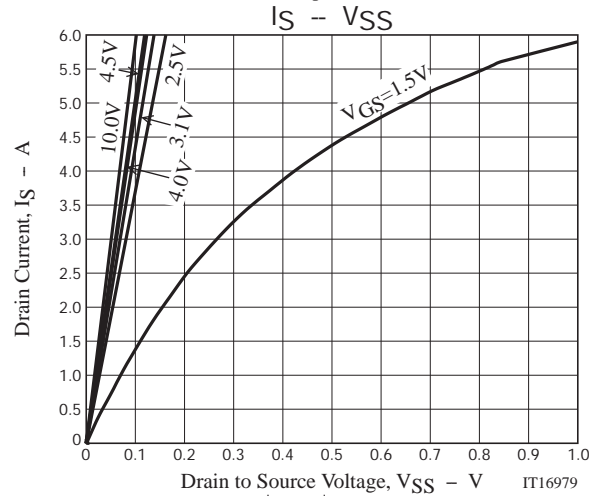
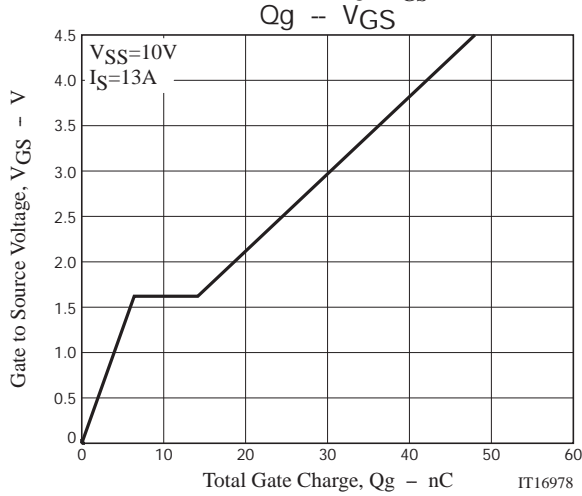
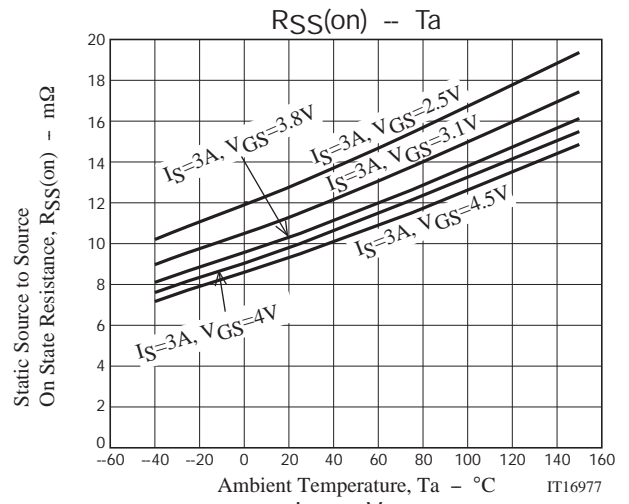
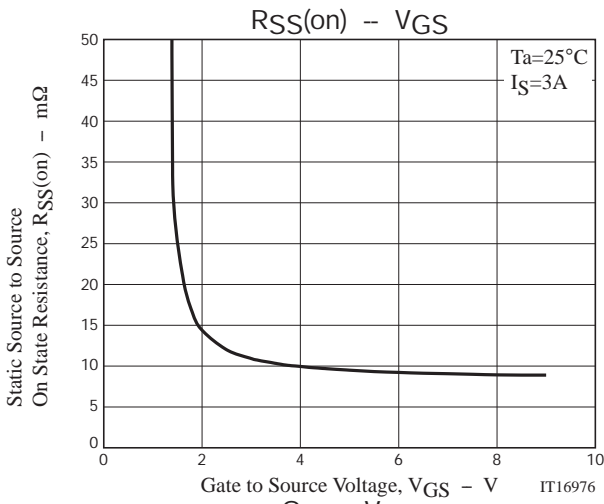
When FET1 is measured, Gate and Source of FET2 are short-circuited.

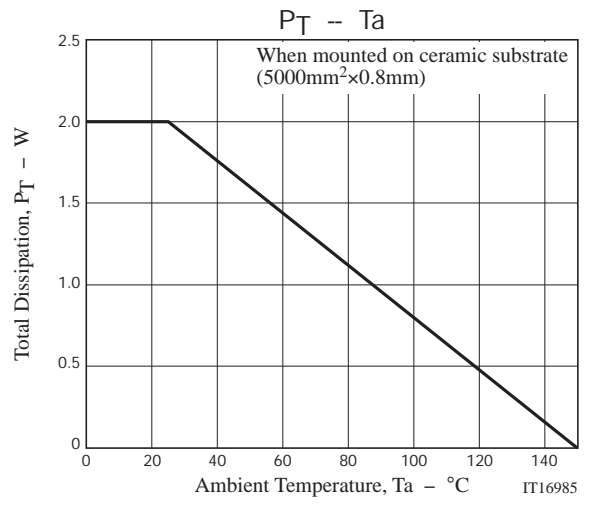
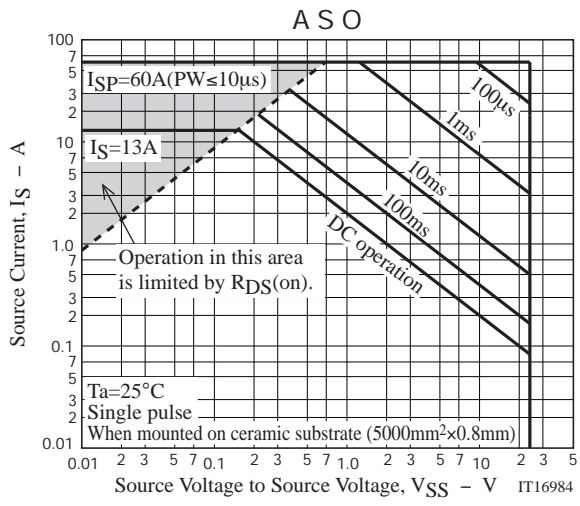
Test Circuit 8  
Qg



When FET1 is measured, Gate and Source of FET2 are short-circuited.

# EFC6601R



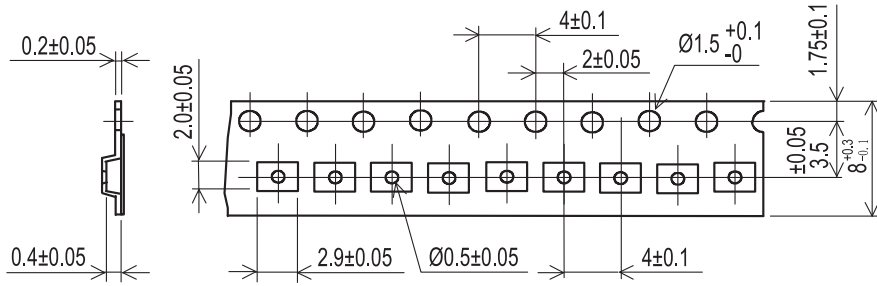


Taping Specification

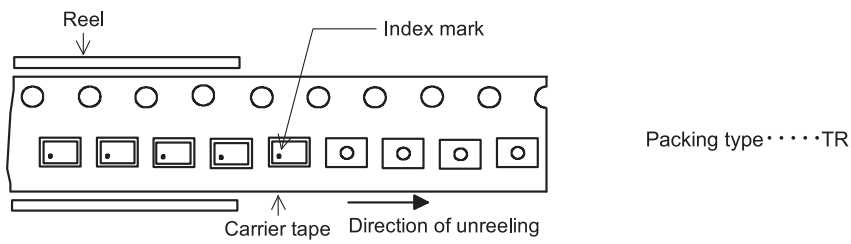
EFC6601R-TR

1. Taping Configuration

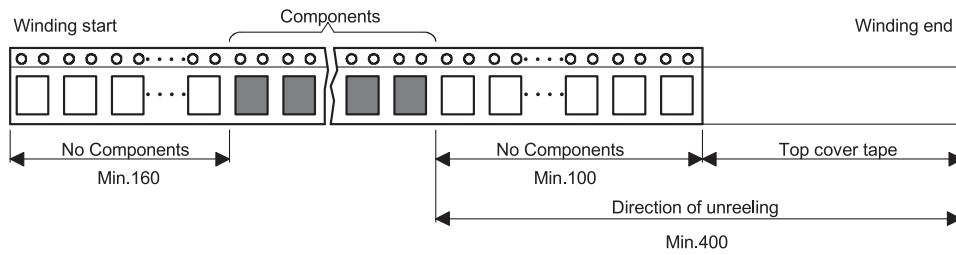
1-1 .Carrier Tape Size (unit:mm)



1-2 .Device Placement Direction



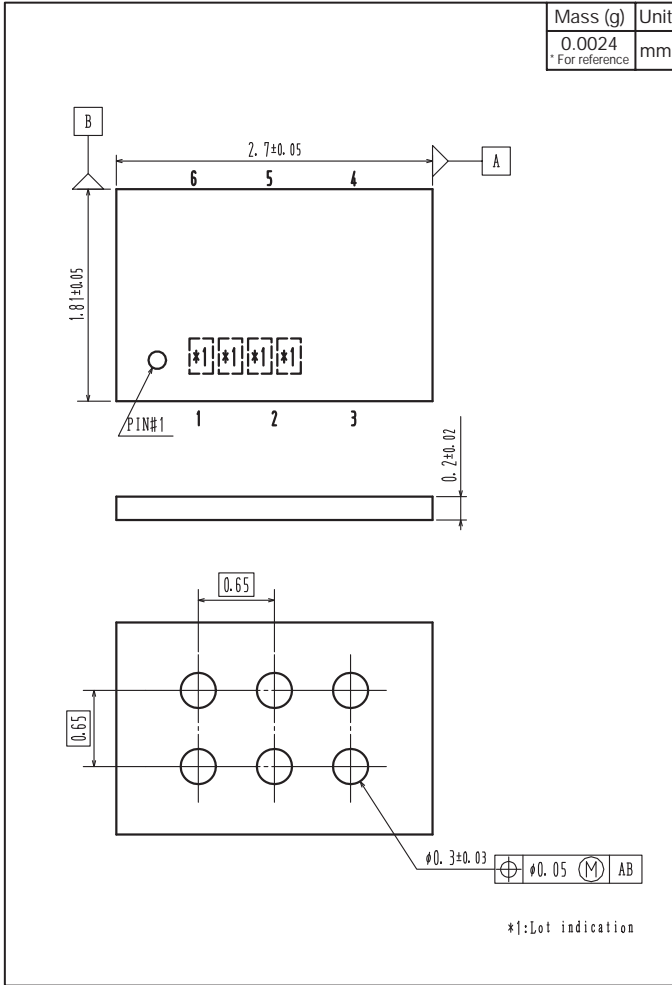
1-3 .Leader portion and Trailer portion (unit:mm)



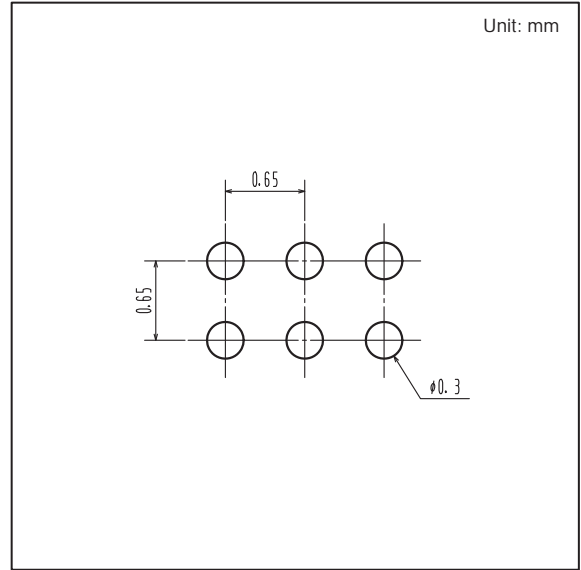
# EFC6601R

## Outline Drawing

EFC6601R-TR



## Land Pattern Example



Note on usage : Since the EFC6601R is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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